

**SEMICONDUCTOR STRUCTURE AND MANUFACTURING METHOD
THEREOF**

ABSTRACT

5

A semiconductor structure and a manufacturing method thereof are provided. The semiconductor structure comprises a cell region, a junction terminal region, a street line and a passivation layer. The junction terminal region is disposed to surround the cell region and has a plurality of guard rings which are
10 disposed in the junction terminal region and surround the cell region. The street line is disposed to surround the junction terminal region. The passivation layer covers the junction terminal region and the street line, and the passivation layer substantially prevents the street line from being damaged due to arcing generated during a high-voltage test.

15

Figure 5